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29. (Amended) A method of inducing a strain by a first element of porous crystalline silicon on a second element, the method comprising the steps of attaching to, or integrally forming with, the first element, the second element, and having at least two electrodes being in electrical contact solely with the first element of the first and second elements, such that subjecting the first element to an electric potential via said at least two electrodes results in a strain induced by the first element on the second element.

REMARKS

Reconsideration of the above identified application in view of this Response is respectfully requested. This Response is in response to the Office Action dated June 05, 2002, hereinafter, referred to as the present Office Action. This Response is also based on the discussion during the telephone interview, conducted on April 25, 2002, *prior to* Applicant's preceding Response communication filed on May 15, 2002, between the Attorney for Applicant, including attendance of the inventor, Dr. Erez Ribak, and, the Examiner, Julio C. Gonzalez, including attendance of the Examiner's supervisor, Nestor Ramirez, during which the Examiner agreed to Applicant's request for filing the indicated preceding Response communication.

In the present Office Action, the Examiner stated the following items:

Item 1: claims 29 - 31 were withdrawn from consideration as being directed to a non-elected invention, according to 37 CFR 1.142(b) and MPEP 821.03.

Item 2: the drawings were objected to under 37 CFR 1.83(a).

Item 3: claims 1 - 3 were rejected under 35 U.S.C. 112, first paragraph, as based on a disclosure which is not enabling.

Item 4: claim 1 was rejected under 35 U.S.C. 102(e) as being anticipated by Takeuchi et al. (U.S. Patent No. 6,265,811 and Takeuchi hereinafter).